

256K x 8 HIGH-SPEED CMOS STATIC RAM

APRIL 2008

FEATURES

- High-speed access time: 8, 10 ns
- Operating Current: 50mA (typ.)
- Standby Current: 700μA (typ.)
- Multiple center power and ground pins for greater noise immunity
- Easy memory expansion with \overline{CE} and \overline{OE} options
- \overline{CE} power-down
- TTL compatible inputs and outputs
- Single 3.3V power supply
- Packages available:
 - 36-pin 400-mil SOJ
 - 44-pin TSOP (Type II)
- Lead-free available

DESCRIPTION

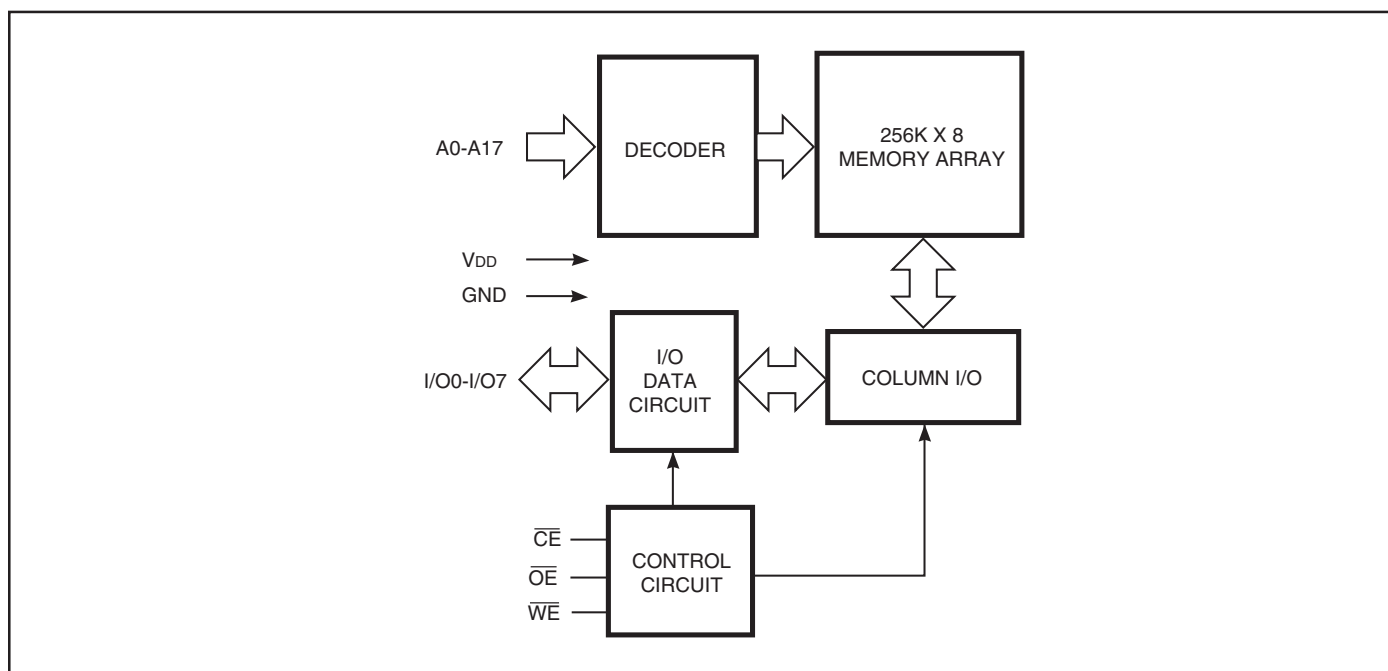
The ISSI IS61LV2568L is a very high-speed, low power, 262,144-word by 8-bit CMOS static RAM. The IS61LV2568L is fabricated using ISSI's high-performance CMOS technology. This highly reliable process coupled with innovative circuit design techniques, yields higher performance and low power consumption devices.

When \overline{CE} is HIGH (deselected), the device assumes a standby mode at which the power dissipation can be reduced down to 36mW (max.) with CMOS input levels.

The IS61LV2568L operates from a single 3.3V power supply and all inputs are TTL-compatible.

The IS61LV2568L is available in 36-pin 400-mil SOJ and 44-pin TSOP (Type II) packages.

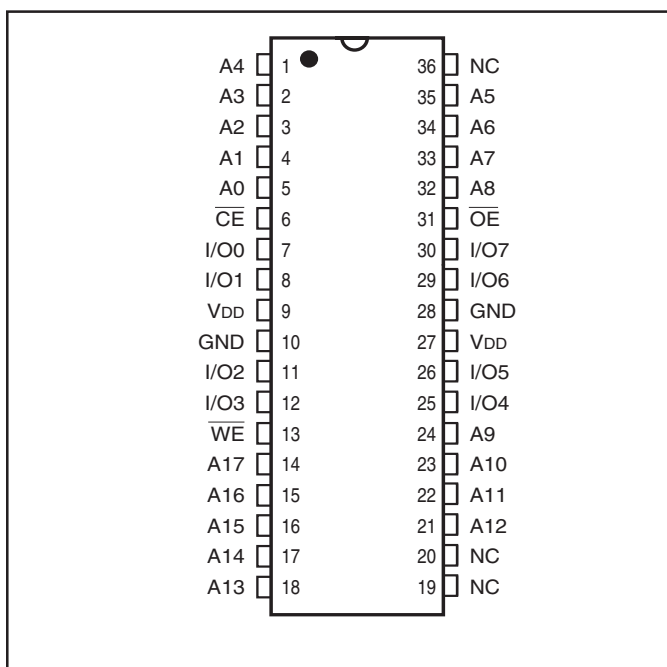
FUNCTIONAL BLOCK DIAGRAM



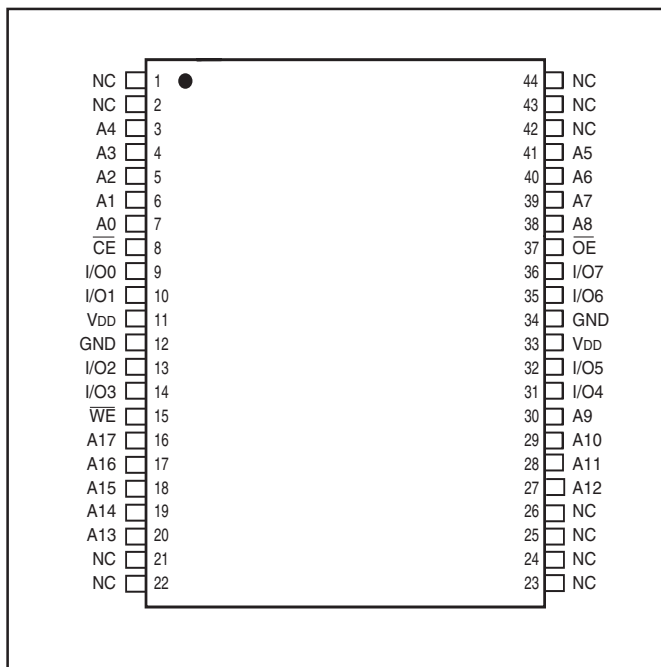
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PIN CONFIGURATION

36-Pin SOJ



44-Pin TSOP (Type II)



PIN DESCRIPTIONS

| | |
|-----------------|---------------------|
| A0-A17 | Address Inputs |
| \overline{CE} | Chip Enable Input |
| \overline{OE} | Output Enable Input |
| \overline{WE} | Write Enable Input |
| I/O0-I/O7 | Bidirectional Ports |
| VDD | Power |
| GND | Ground |
| NC | No Connection |

TRUTH TABLE

| Mode | \overline{WE} | \overline{CE} | \overline{OE} | I/O Operation | V _{DD} Current |
|------------------------------|-----------------|-----------------|-----------------|------------------|-------------------------------------|
| Not Selected (Power-down) | X | H | X | High-Z | I _{SB1} , I _{SB2} |
| Output Disabled | H | L | H | High-Z | I _{CC} |
| Read | H | L | L | D _{OUT} | I _{CC} |
| Write | L | L | X | D _{IN} | I _{CC} |

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

| Symbol | Parameter | Value | Unit |
|-------------------|--------------------------------------|-------------------------------|------|
| V _{DD} | Supply voltage with Respect to GND | -0.5 to +4.0 | V |
| V _{TERM} | Terminal Voltage with Respect to GND | -0.5 to V _{DD} + 0.5 | V |
| T _{STG} | Storage Temperature | -65 to +150 | °C |
| P _D | Power Dissipation | 1.0 | W |

Notes:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

OPERATING RANGE

| Range | Ambient Temperature | V _{DD} (8ns) | V _{DD} (10 ns) |
|------------|---------------------|-----------------------|-------------------------|
| Commercial | 0°C to +70°C | 3.3V +10%,-5% | 3.3V ± 10% |
| Industrial | -40°C to +85°C | | 3.3V ± 10% |

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

| Symbol | Parameter | Test Conditions | Min. | Max. | Unit |
|-----------------|-----------------------------------|---|------|-----------------------|------|
| V _{OH} | Output HIGH Voltage | V _{DD} = Min., I _{OH} = -4.0 mA | 2.4 | — | V |
| V _{OL} | Output LOW Voltage | V _{DD} = Min., I _{OL} = 8.0 mA | — | 0.4 | V |
| V _{IH} | Input HIGH Voltage ⁽¹⁾ | | 2.0 | V _{DD} + 0.3 | V |
| V _{IL} | Input LOW Voltage ⁽¹⁾ | | -0.3 | 0.8 | V |
| I _{LI} | Input Leakage | GND ≤ V _{IN} ≤ V _{DD} | -1 | 1 | μA |
| I _{LO} | Output Leakage | GND ≤ V _{OUT} ≤ V _{DD} , Outputs Disabled | -1 | 1 | μA |

Note:

1. V_{IL}(min) = -0.3V (DC); V_{IL}(min) = -2.0V (pulse width - 2.0 ns).
V_{IH}(max) = V_{DD} + 0.3V (DC); V_{IH}(max) = V_{DD} + 2.0V (pulse width - 2.0 ns).

POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

| Symbol | Parameter | Test Conditions | | -8 ns | | -10 ns | | Unit |
|------------------|--|--|---------------------|-------|------|--------|------|---------|
| | | | | Min. | Max. | Min. | Max. | |
| I _{CC} | V _{DD} Operating Supply Current | V _{DD} = Max., \overline{CE} = V _{IL} I _{OUT} = 0 mA, f = Max. | Com. | — | 65 | — | 60 | mA |
| | | | Ind. | — | — | — | 65 | |
| | | | typ. ⁽²⁾ | — | 50 | — | 50 | |
| I _{SB1} | TTL Standby Current (TTL Inputs) | V _{DD} = Max., V _{IN} = V _{IH} or V _{IL} $\overline{CE} \geq V_{IH}$, f = max | Com. | — | 30 | — | 25 | mA |
| | | | Ind. | — | — | — | 30 | |
| I _{SB2} | CMOS Standby Current (CMOS Inputs) | V _{DD} = Max., $\overline{CE} \geq V_{DD} - 0.2V$, V _{IN} \geq V _{DD} - 0.2V, or V _{IN} \leq 0.2V, f = 0 | Com. | — | 3 | — | 3 | mA |
| | | | Ind. | — | — | — | 4 | mA |
| | | | typ. ⁽²⁾ | — | 700 | — | 700 | μ A |

Note:

- At f = f_{MAX}, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.
- Typical values are measured at V_{DD}=3.3V, T_A=25°C. Not 100% tested.

CAPACITANCE^(1,2)

| Symbol | Parameter | Conditions | Max. | Unit |
|------------------|--------------------------|-----------------------|------|------|
| C _{IN} | Input Capacitance | V _{IN} = 0V | 6 | pF |
| C _{I/O} | Input/Output Capacitance | V _{OUT} = 0V | 8 | pF |

Notes:

- Tested initially and after any design or process changes that may affect these parameters.
- Test conditions: T_A = 25°C, f = 1 MHz, V_{DD} = 3.3V.

AC TEST CONDITIONS

| Parameter | Unit |
|--|---------------------|
| Input Pulse Level | 0V to 3.0V |
| Input Rise and Fall Times | 3 ns |
| Input and Output Timing and Reference Levels | 1.5V |
| Output Load | See Figures 1 and 2 |

AC TEST LOADS

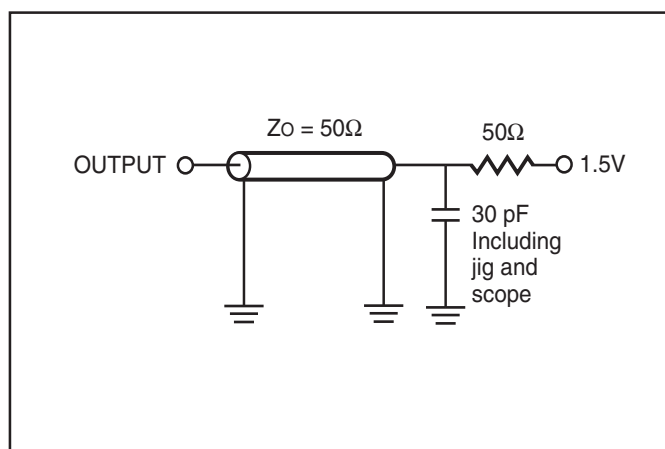


Figure 1

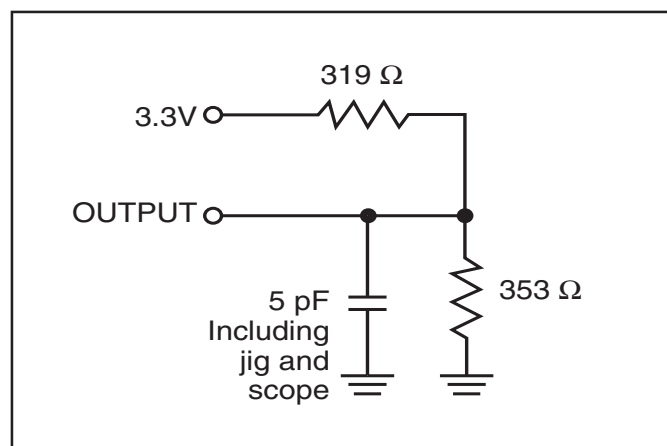


Figure 2

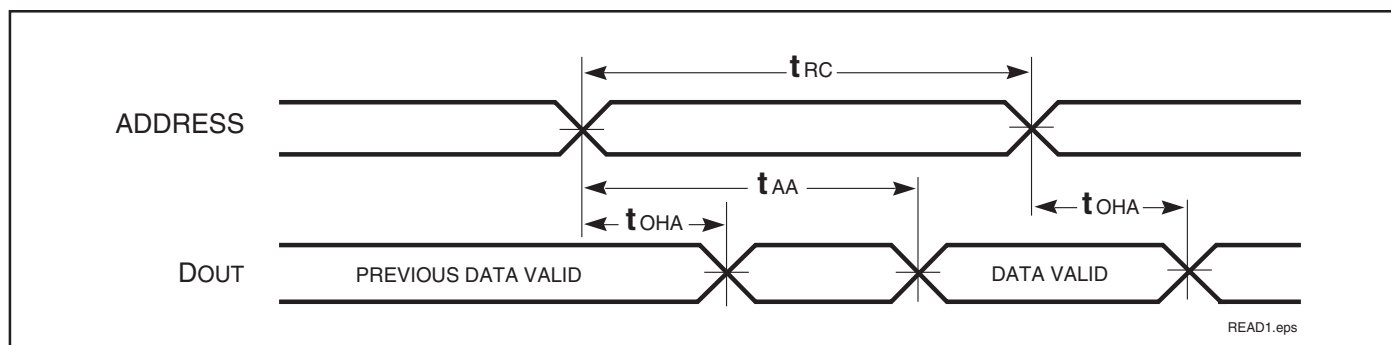
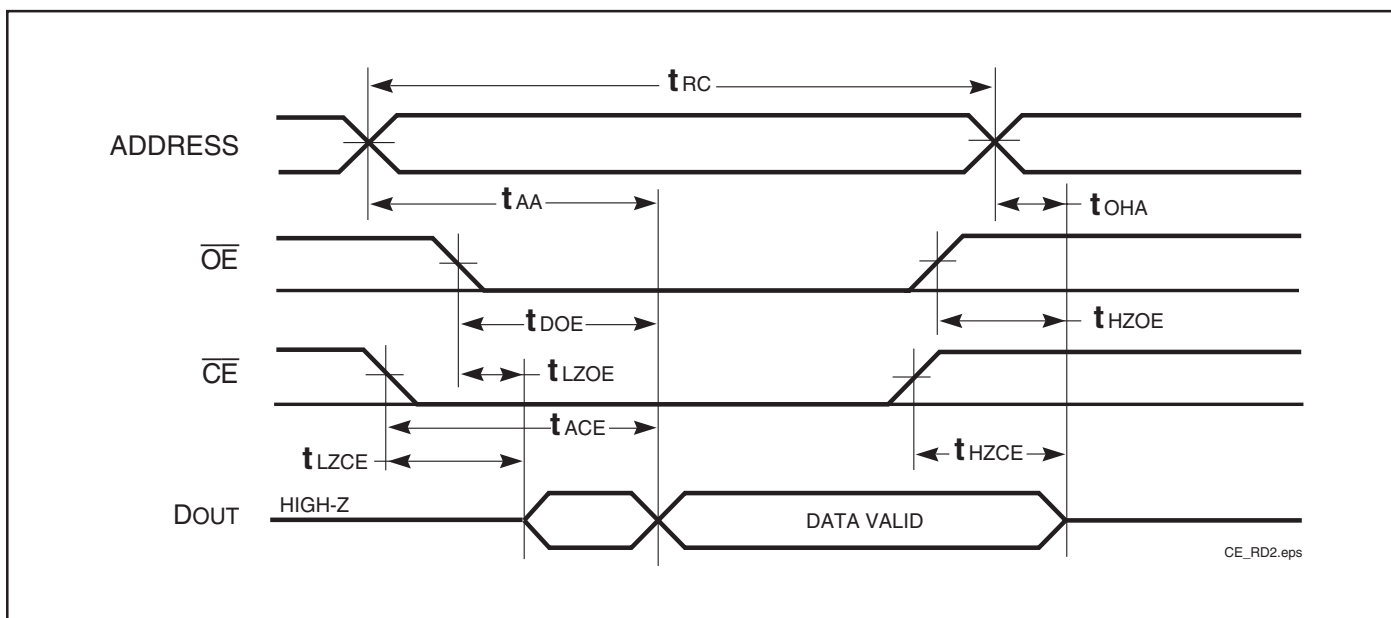
READ CYCLE SWITCHING CHARACTERISTICS⁽¹⁾ (Over Operating Range)

| Symbol | Parameter | - 8 ns | | -10 ns | | Unit |
|----------------------------------|---|--------|-----|--------|------|------|
| | | Min. | Max | Min. | Max. | |
| t _{RC} | Read Cycle Time | 8 | — | 10 | — | ns |
| t _{AA} | Address Access Time | — | 8 | — | 10 | ns |
| t _{OH} | Output Hold Time | 2.5 | — | 2.5 | — | ns |
| t _{ACE} | $\overline{\text{CE}}$ Access Time | — | 8 | — | 10 | ns |
| t _{DOE} | $\overline{\text{OE}}$ Access Time | — | 3.5 | — | 4 | ns |
| t _{LZOE} ⁽²⁾ | $\overline{\text{OE}}$ to Low-Z Output | 0 | — | 0 | — | ns |
| t _{HZOE} ⁽²⁾ | $\overline{\text{OE}}$ to High-Z Output | 0 | 3.5 | 0 | 4 | ns |
| t _{LZCE} ⁽²⁾ | $\overline{\text{CE}}$ to Low-Z Output | 3.5 | — | 3 | — | ns |
| t _{HZCE} ⁽²⁾ | $\overline{\text{CE}}$ to High-Z Output | 0 | 3.5 | 0 | 4 | ns |

Notes:

1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1.
2. Tested with the load in Figure 2. Transition is measured ± 200 mV from steady-state voltage. Not 100% tested.

AC WAVEFORMS

READ CYCLE NO. 1^(1,2) (Address Controlled) ($\overline{CE} = \overline{OE} = V_{IL}$)READ CYCLE NO. 2^(1,3) (\overline{CE} and \overline{OE} Controlled)

Notes:

1. \overline{WE} is HIGH for a Read Cycle.
2. The device is continuously selected. \overline{OE} , $\overline{CE} = V_{IL}$.
3. Address is valid prior to or coincident with \overline{CE} LOW transitions.

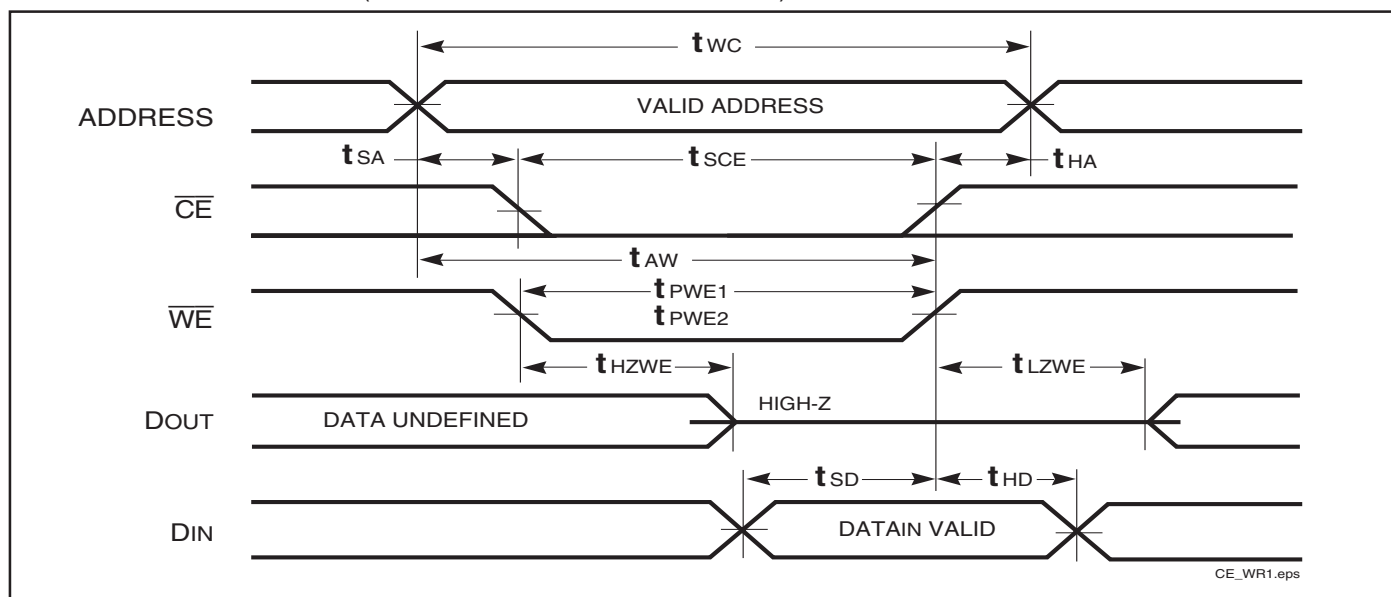
WRITE CYCLE SWITCHING CHARACTERISTICS^(1,2) (Over Operating Range)

| Symbol | Parameter | - 8 ns | | -10 ns | | Unit |
|----------------------------------|---|--------|-----|--------|------|------|
| | | Min. | Max | Min. | Max. | |
| t _{WC} | Write Cycle Time | 8 | — | 10 | — | ns |
| t _{SCE} | \overline{CE} to Write End | 7 | — | 8 | — | ns |
| t _{AW} | Address Setup Time to Write End | 7 | — | 8 | — | ns |
| t _{HA} | Address Hold from Write End | 0 | — | 0 | — | ns |
| t _{SA} | Address Setup Time | 0 | — | 0 | — | ns |
| t _{PWE1} | \overline{WE} Pulse Width (\overline{OE} = HIGH) | 6 | — | 7 | — | ns |
| t _{PWE2} | \overline{WE} Pulse Width (\overline{OE} = LOW) | 6.5 | — | 8 | — | ns |
| t _{SD} | Data Setup to Write End | 4 | — | 5 | — | ns |
| t _{HD} | Data Hold from Write End | 0 | — | 0 | — | ns |
| t _{HZWE} ⁽³⁾ | \overline{WE} LOW to High-Z Output | — | 3 | — | 4 | ns |
| t _{LZWE} ⁽³⁾ | \overline{WE} HIGH to Low-Z Output | 0 | — | 0 | — | ns |

Notes:

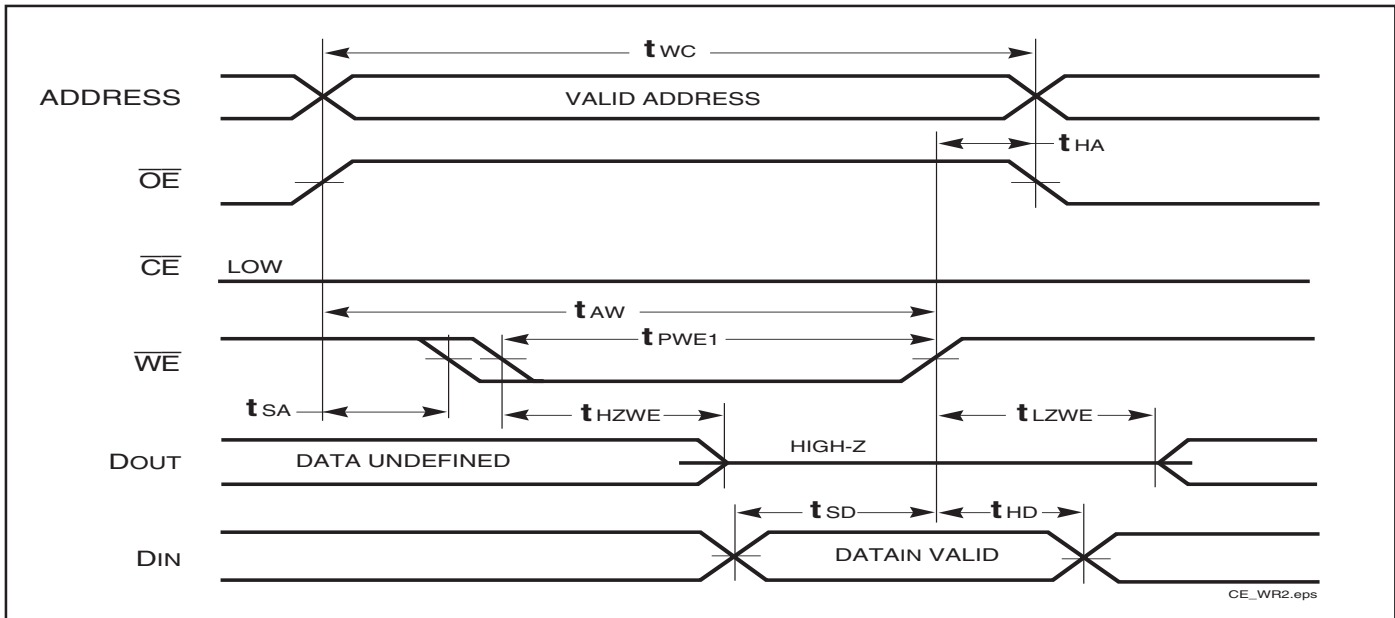
1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1.
2. The internal write time is defined by the overlap of \overline{CE} LOW and \overline{WE} LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the Write.
3. Tested with the load in Figure 2. Transition is measured ± 500 mV from steady-state voltage. Not 100% tested.

AC WAVEFORMS

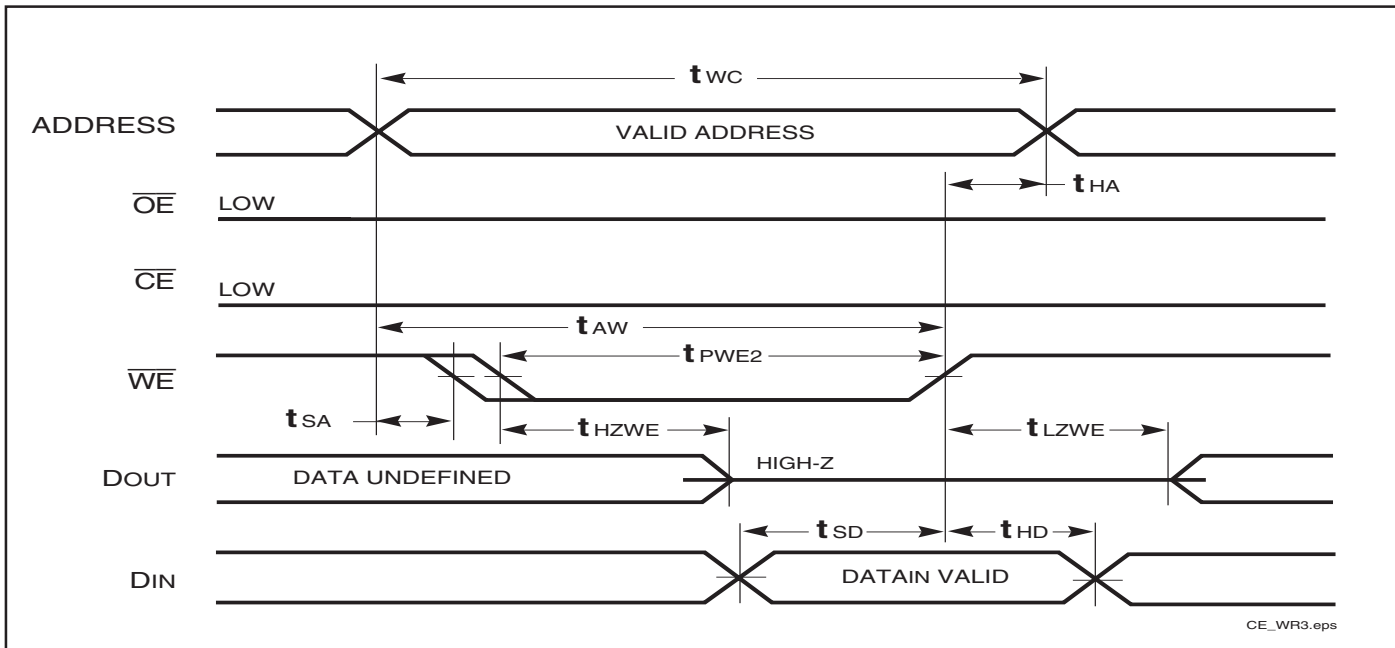
WRITE CYCLE NO. 1^(1,2) (\overline{CE} Controlled, \overline{OE} = HIGH or LOW)**Note:**

1. The internal Write time is defined by the overlap of \overline{CE} = LOW and \overline{WE} = LOW. All signals must be in valid states to initiate a Write, but any can be deasserted to terminate the Write. The Data Input Setup and Hold timing is referenced to the rising or falling edge of the signal that terminates the Write.

AC WAVEFORMS

WRITE CYCLE NO. 2⁽¹⁾ (\overline{WE} Controlled, \overline{OE} = HIGH during Write Cycle)**Note:**

1. The internal Write time is defined by the overlap of \overline{CE} = LOW and \overline{WE} = LOW. All signals must be in valid states to initiate a Write, but any can be deasserted to terminate the Write. The Data Input Setup and Hold timing is referenced to the rising or falling edge of the signal that terminates the Write.

WRITE CYCLE NO. 3 (\overline{WE} Controlled: \overline{OE} is LOW During Write Cycle)**Note:**

1. The internal Write time is defined by the overlap of \overline{CE} = LOW and \overline{WE} = LOW. All signals must be in valid states to initiate a Write, but any can be deasserted to terminate the Write. The Data Input Setup and Hold timing is referenced to the rising or falling edge of the signal that terminates the Write.

ORDERING INFORMATION**Commercial Range: 0°C to +70°C**

| Speed (ns) | Order Part No. | Package |
|------------|------------------|---------------------------|
| 8 | IS61LV2568L-8K | 400-mil SOJ |
| | IS61LV2568L-8T | TSOP (Type II) |
| | IS61LV2568L-8TL | TSOP (Type II), Lead-free |
| 10 | IS61LV2568L-10T | TSOP (Type II) |
| | IS61LV2568L-10TL | TSOP (Type II), Lead-free |

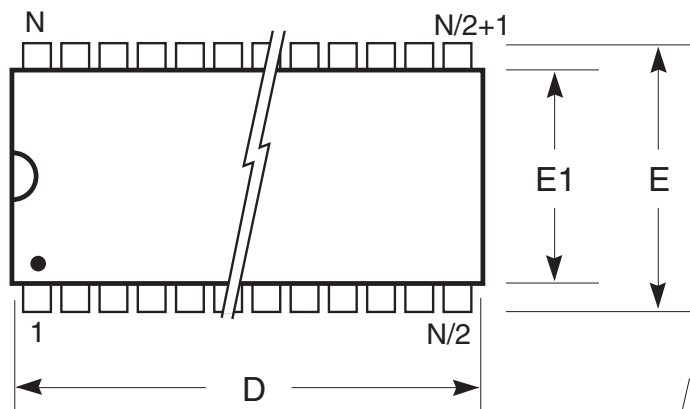
Industrial Range: -40°C to +85°C

| Speed (ns) | Order Part No. | Package |
|------------|-------------------|------------------------|
| 10 | IS61LV2568L-10KI | 400-mil SOJ |
| | IS61LV2568L-10KLI | 400-mil SOJ, Lead-free |

PACKAGING INFORMATION

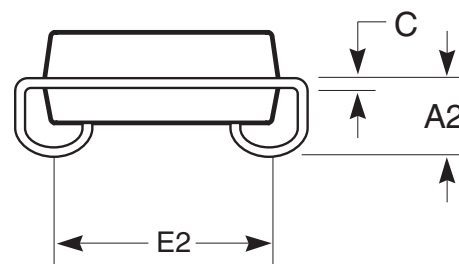
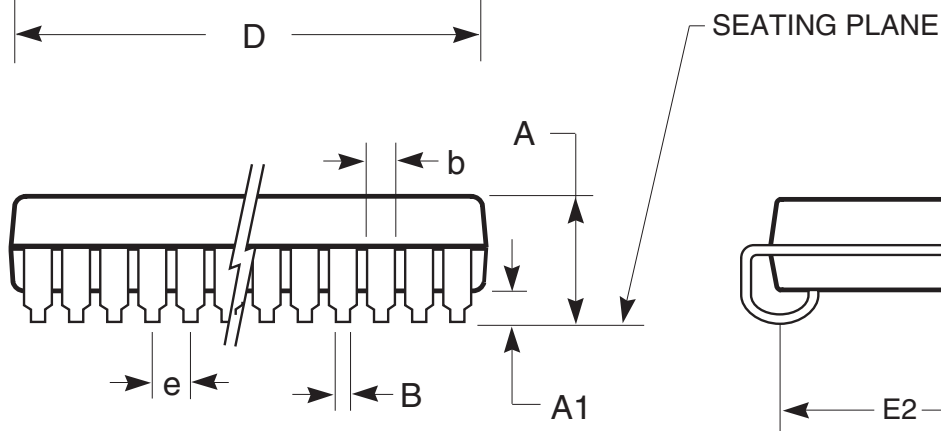
400-mil Plastic SOJ

Package Code: K



Notes:

1. Controlling dimension: millimeters.
2. BSC = Basic lead spacing between centers.
3. Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
4. Reference document: JEDEC MS-027.



| Symbol | Millimeters | | Inches | | Symbol | Millimeters | | Inches | | Symbol | Millimeters | | Inches | |
|---------------|-------------|-------|-----------|-------|--------|-------------|-------|-----------|-------|--------|-------------|-------|-----------|-------|
| | Min | Max | Min | Max | | Min | Max | Min | Max | | Min | Max | Min | Max |
| No. Leads (N) | | 28 | | | 32 | | | 36 | | | | | | |
| A | 3.25 | 3.75 | 0.128 | 0.148 | A | 3.25 | 3.75 | 0.128 | 0.148 | A | 3.25 | 3.75 | 0.128 | 0.148 |
| A1 | 0.64 | — | 0.025 | — | A1 | 0.64 | — | 0.025 | — | A1 | 0.64 | — | 0.025 | — |
| A2 | 2.08 | — | 0.082 | — | A2 | 2.08 | — | 0.082 | — | A2 | 2.08 | — | 0.082 | — |
| B | 0.38 | 0.51 | 0.015 | 0.020 | B | 0.38 | 0.51 | 0.015 | 0.020 | B | 0.38 | 0.51 | 0.015 | 0.020 |
| b | 0.66 | 0.81 | 0.026 | 0.032 | b | 0.66 | 0.81 | 0.026 | 0.032 | b | 0.66 | 0.81 | 0.026 | 0.032 |
| C | 0.18 | 0.33 | 0.007 | 0.013 | C | 0.18 | 0.33 | 0.007 | 0.013 | C | 0.18 | 0.33 | 0.007 | 0.013 |
| D | 18.29 | 18.54 | 0.720 | 0.730 | D | 20.82 | 21.08 | 0.820 | 0.830 | D | 23.37 | 23.62 | 0.920 | 0.930 |
| E | 11.05 | 11.30 | 0.435 | 0.445 | E | 11.05 | 11.30 | 0.435 | 0.445 | E | 11.05 | 11.30 | 0.435 | 0.445 |
| E1 | 10.03 | 10.29 | 0.395 | 0.405 | E1 | 10.03 | 10.29 | 0.395 | 0.405 | E1 | 10.03 | 10.29 | 0.395 | 0.405 |
| E2 | 9.40 BSC | | 0.370 BSC | | E2 | 9.40 BSC | | 0.370 BSC | | E2 | 9.40 BSC | | 0.370 BSC | |
| e | 1.27 BSC | | 0.050 BSC | | e | 1.27 BSC | | 0.050 BSC | | e | 1.27 BSC | | 0.050 BSC | |

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Rev. F
10/29/03



PACKAGING INFORMATION

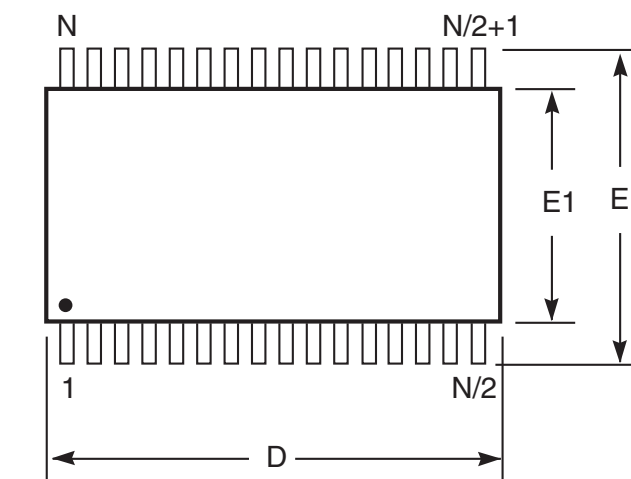
| Symbol | Millimeters | | Inches | | Millimeters | | Inches | | Millimeters | | Inches | |
|---------------|-------------|-------|-----------|-------|-------------|-------|-----------|-------|-------------|-------|-----------|-------|
| | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max |
| No. Leads (N) | 40 | | | | 42 | | | | 44 | | | |
| A | 3.25 | 3.75 | 0.128 | 0.148 | 3.25 | 3.75 | 0.128 | 0.148 | 3.25 | 3.75 | 0.128 | 0.148 |
| A1 | 0.64 | — | 0.025 | — | 0.64 | — | 0.025 | — | 0.64 | — | 0.025 | — |
| A2 | 2.08 | — | 0.082 | — | 2.08 | — | 0.082 | — | 2.08 | — | 0.082 | — |
| B | 0.38 | 0.51 | 0.015 | 0.020 | 0.38 | 0.51 | 0.015 | 0.020 | 0.38 | 0.51 | 0.015 | 0.020 |
| b | 0.66 | 0.81 | 0.026 | 0.032 | 0.66 | 0.81 | 0.026 | 0.032 | 0.66 | 0.81 | 0.026 | 0.032 |
| C | 0.18 | 0.33 | 0.007 | 0.013 | 0.18 | 0.33 | 0.007 | 0.013 | 0.18 | 0.33 | 0.007 | 0.013 |
| D | 25.91 | 26.16 | 1.020 | 1.030 | 27.18 | 27.43 | 1.070 | 1.080 | 28.45 | 28.70 | 1.120 | 1.130 |
| E | 11.05 | 11.30 | 0.435 | 0.445 | 11.05 | 11.30 | 0.435 | 0.445 | 11.05 | 11.30 | 0.435 | 0.445 |
| E1 | 10.03 | 10.29 | 0.395 | 0.405 | 10.03 | 10.29 | 0.395 | 0.405 | 10.03 | 10.29 | 0.395 | 0.405 |
| E2 | 9.40 BSC | | 0.370 BSC | | 9.40 BSC | | 0.370 BSC | | 9.40 BSC | | 0.370 BSC | |
| e | 1.27 BSC | | 0.050 BSC | | 1.27 BSC | | 0.050 BSC | | 1.27 BSC | | 0.050 BSC | |

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PACKAGING INFORMATION

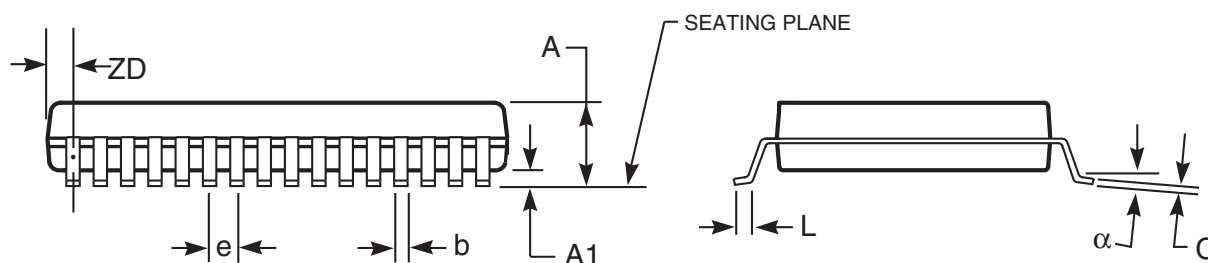
Plastic TSOP

Package Code: T (Type II)



Notes:

1. Controlling dimension: millimeters, unless otherwise specified.
2. BSC = Basic lead spacing between centers.
3. Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
4. Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.



Plastic TSOP (T - Type II)

| Symbol | Millimeters | | Inches | | Millimeters | | Inches | | Millimeters | | Inches | |
|---------------|-------------|-------|-----------|-------|-------------|-------|-----------|-------|-------------|-------|-----------|-------|
| | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max |
| Ref. Std. | | | | | | | | | | | | |
| No. Leads (N) | 32 | | | | 44 | | | | 50 | | | |
| A | — | 1.20 | — | 0.047 | — | 1.20 | — | 0.047 | — | 1.20 | — | 0.047 |
| A1 | 0.05 | 0.15 | 0.002 | 0.006 | 0.05 | 0.15 | 0.002 | 0.006 | 0.05 | 0.15 | 0.002 | 0.006 |
| b | 0.30 | 0.52 | 0.012 | 0.020 | 0.30 | 0.45 | 0.012 | 0.018 | 0.30 | 0.45 | 0.012 | 0.018 |
| C | 0.12 | 0.21 | 0.005 | 0.008 | 0.12 | 0.21 | 0.005 | 0.008 | 0.12 | 0.21 | 0.005 | 0.008 |
| D | 20.82 | 21.08 | 0.820 | 0.830 | 18.31 | 18.52 | 0.721 | 0.729 | 20.82 | 21.08 | 0.820 | 0.830 |
| E1 | 10.03 | 10.29 | 0.391 | 0.400 | 10.03 | 10.29 | 0.395 | 0.405 | 10.03 | 10.29 | 0.395 | 0.405 |
| E | 11.56 | 11.96 | 0.451 | 0.466 | 11.56 | 11.96 | 0.455 | 0.471 | 11.56 | 11.96 | 0.455 | 0.471 |
| e | 1.27 BSC | | 0.050 BSC | | 0.80 BSC | | 0.032 BSC | | 0.80 BSC | | 0.031 BSC | |
| L | 0.40 | 0.60 | 0.016 | 0.024 | 0.41 | 0.60 | 0.016 | 0.024 | 0.40 | 0.60 | 0.016 | 0.024 |
| ZD | 0.95 REF | | 0.037 REF | | 0.81 REF | | 0.032 REF | | 0.88 REF | | 0.035 REF | |
| α | 0° | 5° | 0° | 5° | 0° | 5° | 0° | 5° | 0° | 5° | 0° | 5° |

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